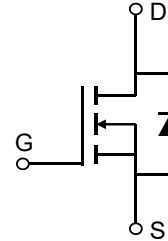


Description

Features

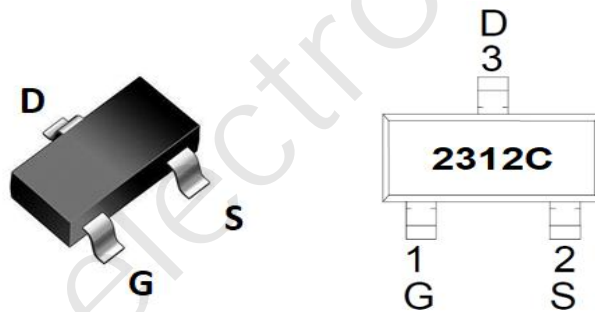
- 20V, 6.5A
 $R_{DS(ON)}$ Typ = 16mΩ @ $V_{GS} = 4.5V$
 $R_{DS(ON)}$ Typ = 20mΩ @ $V_{GS} = 2.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMLTU2312C	2312C	SOT-23	TAPING	13"	3000	120000

Absolute Maximum Ratings (@ $T_J = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	20	V
V_{GS}	Gate-to-Source Voltage	±12	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	6.5
		$T_A = 100^\circ C$	3.9
I_{DM}	Pulsed Drain Current ⁽¹⁾	26	A
P_D	Power Dissipation	$T_A = 25^\circ C$	1.25
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽²⁾	100	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	°C

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
--------	-----------	------------	------	------	------	------

Off Characteristics

$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 20\text{V}$, $V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 12\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	0.4	0.7	1	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽³⁾	$V_{GS} = 4.5\text{V}$, $I_D = 2\text{A}$	-	16	21	mΩ
		$V_{GS} = 2.5\text{V}$, $I_D = 1.5\text{A}$	-	20	26	mΩ

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 10\text{V}$, $f = 1\text{MHz}$	-	594	-	pF
C_{oss}	Output Capacitance		-	77	-	pF
C_{rss}	Reverse Transfer Capacitance		-	67	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0$ to 4.5V $V_{DS} = 10\text{V}$, $I_D = 3\text{A}$	-	7.5	-	nC
Q_{gs}	Gate Source Charge		-	1.3	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	2	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 4.5\text{V}$, $V_{DD} = 10\text{V}$ $I_D = 3\text{A}$, $R_{GEN} = 3\Omega$	-	4.2	-	ns
t_r	Turn-On Rise Time		-	13	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	18	-	ns
t_f	Turn-Off Fall Time		-	5.8	-	ns

Drain-Source Diode Characteristics and Max Ratings

I_S	Maximum Continuous Drain to Source Diode Forward Current	$V_{GS} = 0\text{V}$, $I_S = 2\text{A}$	-	-	6.5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	26	A
V_{SD}	Drain to Source Diode Forward Voltage		-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time		-	5.8	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	1.7	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Typical Performance Characteristics

Figure 1: Output Characteristics

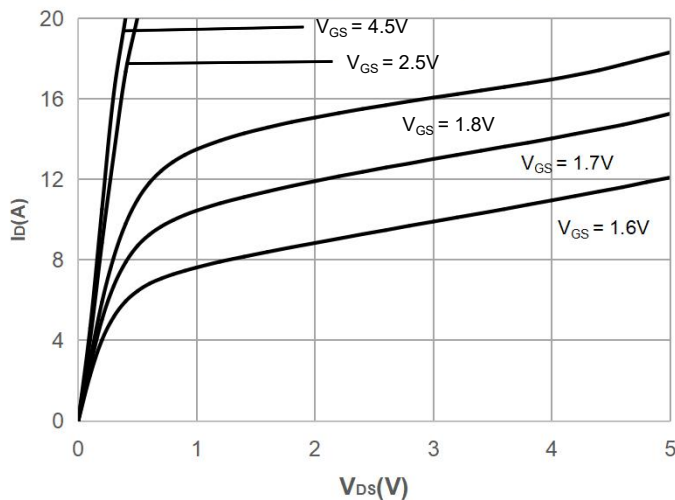


Figure 2: Typical Transfer Characteristics

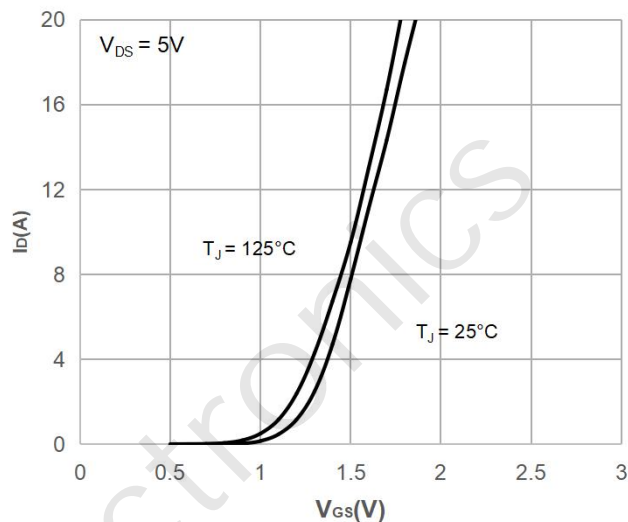


Figure 3: On-resistance vs. Drain Current

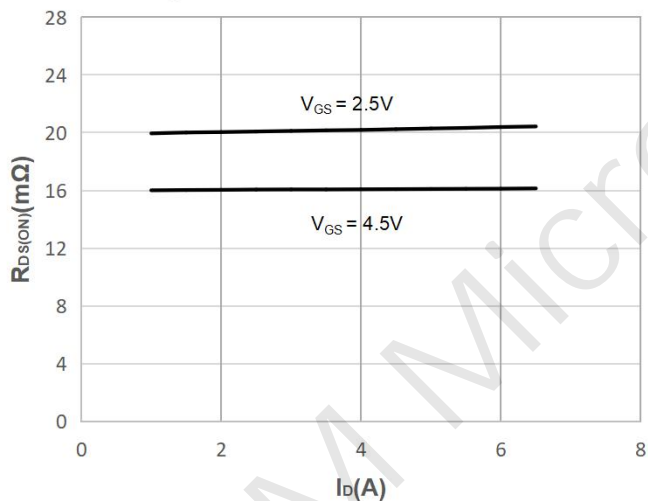


Figure 4: Body Diode Characteristics

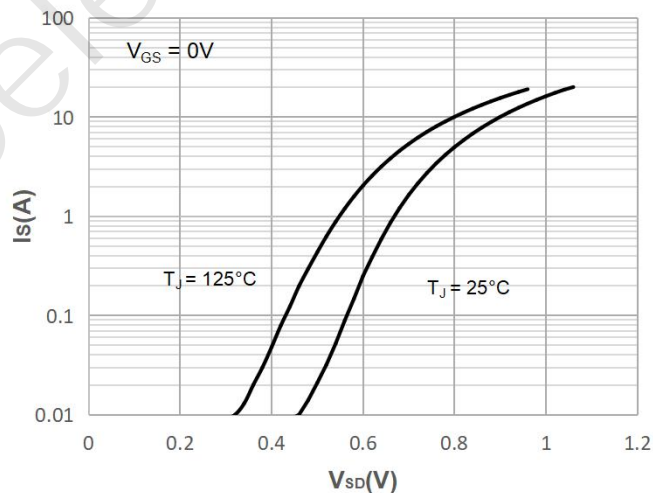


Figure 5: Gate Charge Characteristics

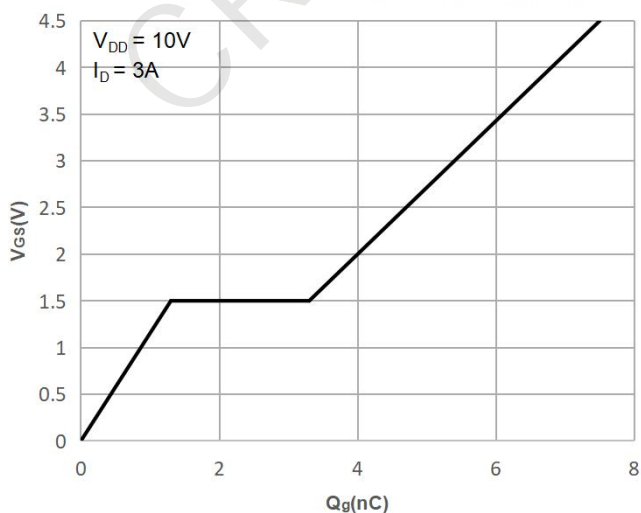
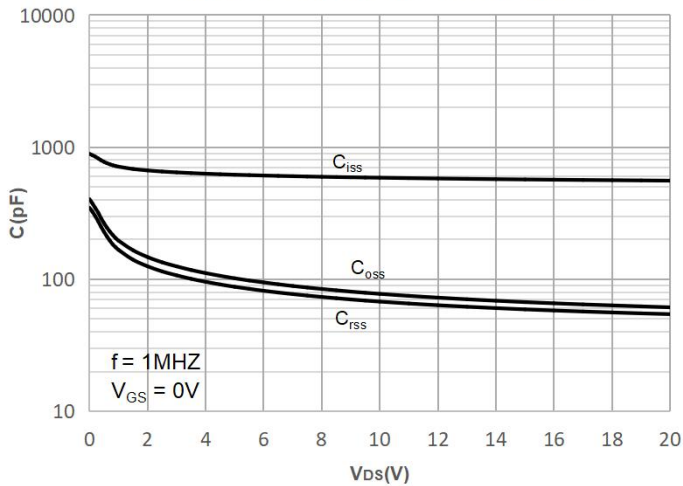


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

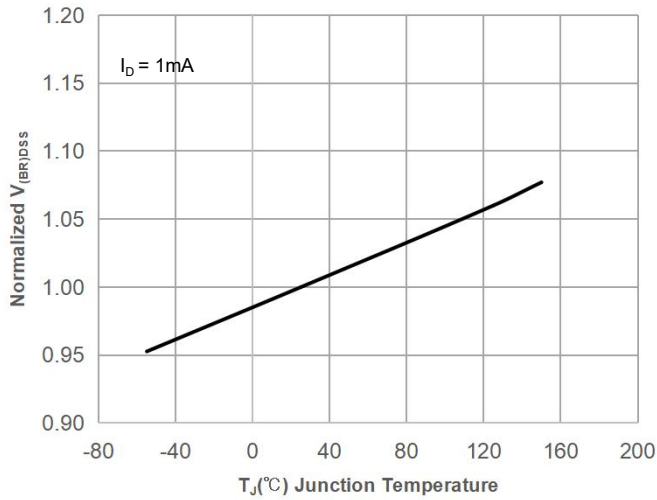


Figure 8: Normalized on Resistance vs. Junction Temperature

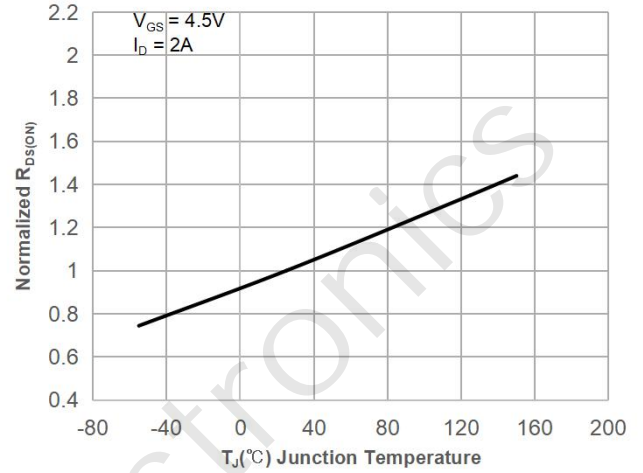


Figure 9: Maximum Safe Operating Area

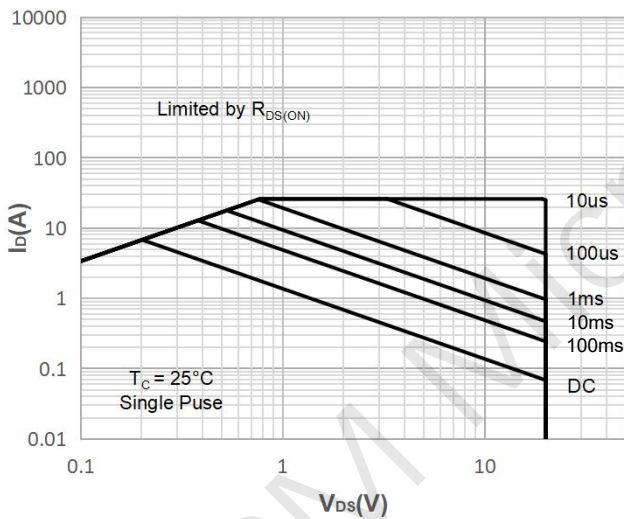


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

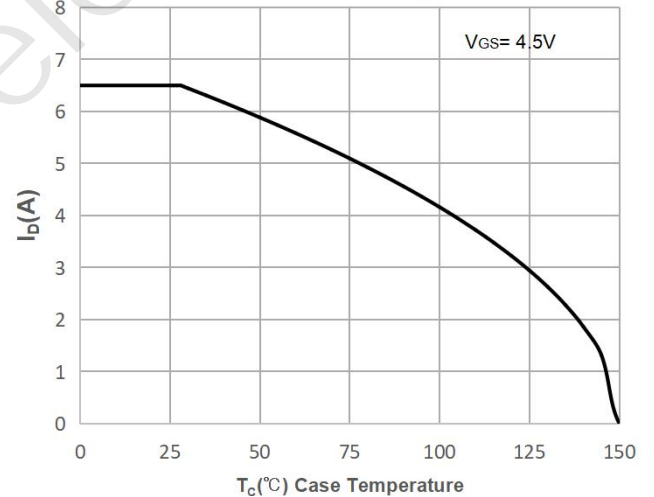


Figure 11: Normalized Maximum Transient Thermal Impedance

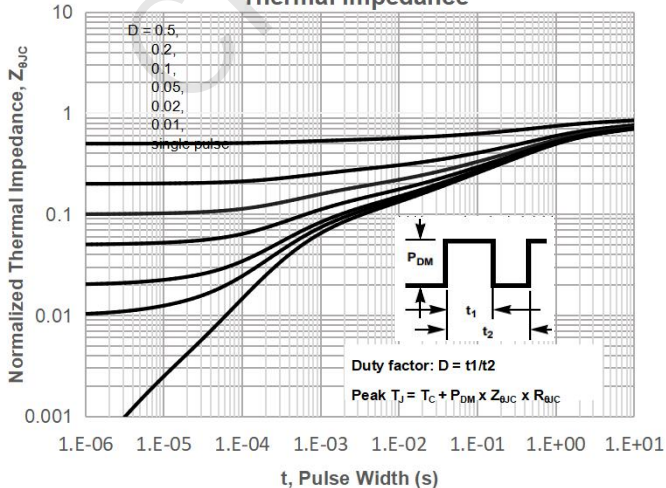
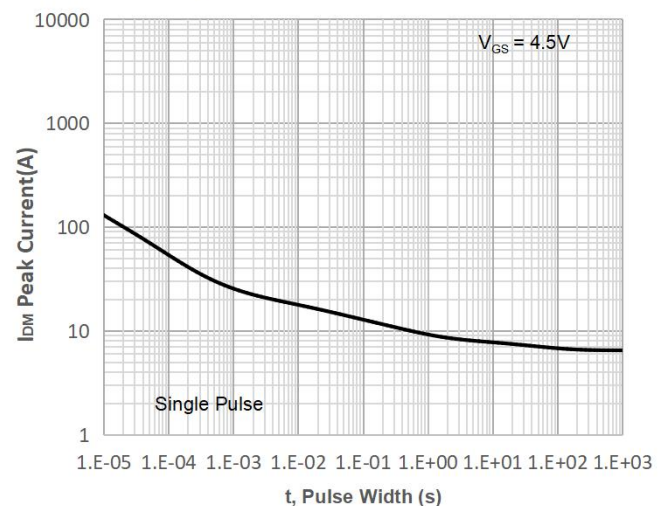


Figure 12: Peak Current Capacity



Test Circuit

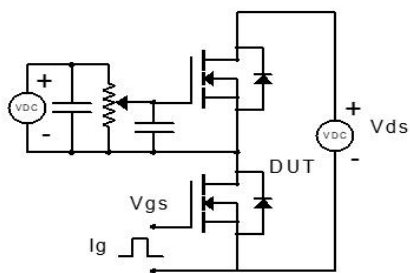


Figure 1: Gate Charge Test Circuit & Waveform



Figure 2: Resistive Switching Test Circuit & Waveform

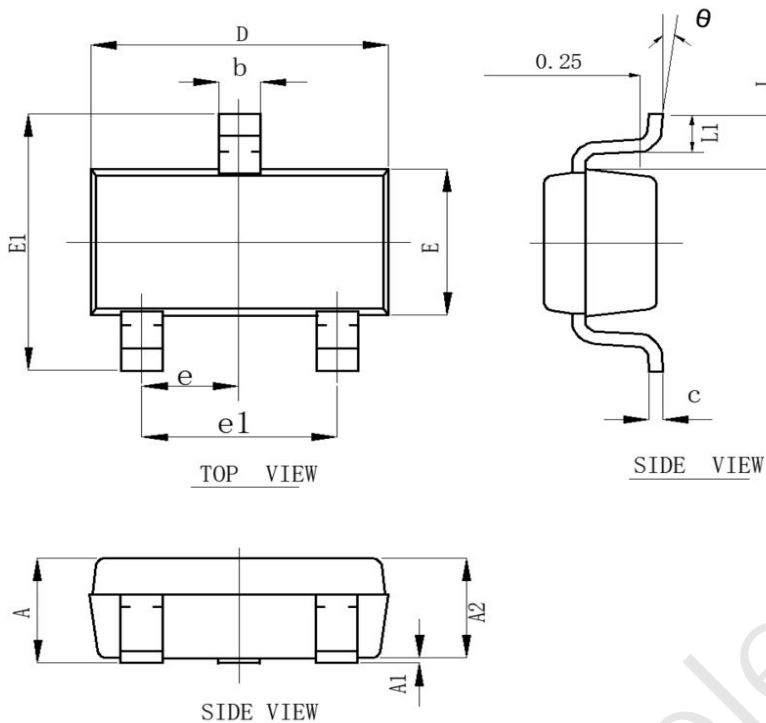


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform



Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOT-23)



COMMON DIMENSIONS In Millimeters		
SYMBOL	MIN	MAX
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
L	0.550	REF.
θ	0°	8°
L1	0.300	0.500
e	0.950 TYP.	
e1	1.800	2.000

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